L Number	Hits	Search Text	DB	Time stamp
9	655258	H01L$4	EPO; JPO; DERWENT	2003/05/05 02:18
10	366362	H01L$4 and semiconductor	EPO; JPO; DERWENT	2003/05/05 02:17
11	523	(H01L$4 and semiconductor) and (self adj aligned adj contact)	EPO; JPO; DERWENT	2003/05/05 02:17
12	2	((H01L$4 and semiconductor) and (self adj aligned adj contact)) and (stopping adj layer)	EPO; JPO; DERWENT	2003/05/05 02:18
15	1748	self adj (aligned or aligning or aligns or align) adj (contact or contacts)	USPAT	2003/05/05 02:26
16	67	(self adj (aligned or aligning or aligns or align) adj (contact or contacts)) and ((dry adj etch$3) with (interdielectric or dielectric))	USPAT	2003/05/05 02:42
17	0	planarizing with (gate adj upper adj dielectric)	USPAT	2003/05/05 02:44
18	0	planarize with (gate adj upper adj dielectric)	USPAT	2003/05/05 02:48
19	0	planar$5 with (gate adj upper adj dielectric)	USPAT	2003/05/05 02:48
20	1	gate adj upper adj dielectric	USPAT	2003/05/05 02:44
21	5361	gate adj dielectric	USPAT	2003/05/05 02:44
22	33	planarizing with (gate adj dielectric)	USPAT	2003/05/05 02:45
23	8	planarize with (gate adj dielectric)	USPAT	2003/05/05 02:48
24	157	planar$5 with (gate adj dielectric)	USPAT	2003/05/05 02:48
25	120	(planar$5 with (gate adj dielectric)) not ((planarize with (gate adj dielectric)) or (planarizing with (gate adj dielectric)))	USPAT	2003/05/05 02:48
29	8	(("6313018") or ("6287957") or ("6165901") or ("6204161") or ("6507064") or ("6468859") or ("6380042") or ("6081016")).PN.	USPAT	2003/05/05 03:42
–	5927	(gate adj electrode) and ((dry adj etching) or CMP or (chemical adj mechanical adj polishing))	USPAT	2003/05/03 21:16
–	19	(gate adj electrode) and (interdielectric) and ((dry adj etching) or CMP or (chemical adj mechanical adj polishing))	USPAT	2002/06/30 17:57
–	31	(gate) and (interdielectric) and ((dry adj etching) or CMP or (chemical adj mechanical adj polishing))	USPAT	2002/06/30 18:01
–	1945	438/586.ccls. or 438/587.ccls. or 438/595.ccls. or 438/597.ccls. or 438/598.ccls.	USPAT	2003/04/16 15:03
–	214	438/584.ccls.	USPAT	2003/04/16 15:02
–	1650	438/666.ccls. or 438/669.ccls. or 438/674.ccls. or 438/684.ccls. or 438/685.ccls.	USPAT	2003/05/05 02:15
–	1791	(438/586.ccls. or 438/587.ccls. or 438/595.ccls. or 438/597.ccls. or 438/598.ccls.) not (438/584.ccls. or (438/666.ccls. or 438/669.ccls. or 438/674.ccls. or 438/684.ccls. or 438/685.ccls.))	USPAT	2003/05/05 03:17
–	175	438/584.ccls. not ((438/586.ccls. or 438/587.ccls. or 438/595.ccls. or 438/597.ccls. or 438/598.ccls.) or (438/666.ccls. or 438/669.ccls. or 438/674.ccls. or 438/684.ccls. or 438/685.ccls.))	USPAT	2003/04/16 15:57
–	1514	(438/666.ccls. or 438/669.ccls. or 438/674.ccls. or 438/684.ccls. or 438/685.ccls.) not ((438/586.ccls. or 438/587.ccls. or 438/595.ccls. or 438/597.ccls. or 438/598.ccls.) or 438/584.ccls.)	USPAT	2003/04/16 16:57
–	290389	gate	USPAT	2003/05/03 21:17
–	21471	gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))	USPAT	2003/05/03 21:47

-	13415	(gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))) and (dielectric or interdielectric)	USPAT	2003/05/03 21:21
-	1564	((gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))) and (dielectric or interdielectric)) and (planariz$3 with ((dry adj etching) or CMP))	USPAT	2003/05/03 21:22
-	630	(((gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))) and (dielectric or interdielectric)) and (planariz$3 with ((dry adj etching) or CMP))) and (conductive with ((doped adj polysilicon) or titanium or (titanium adj nitride) or tungsten))	USPAT	2003/05/03 21:39
-	89	((((gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))) and (dielectric or interdielectric)) and (planariz$3 with ((dry adj etching) or CMP))) and (conductive with ((doped adj polysilicon) or titanium or (titanium adj nitride) or tungsten))) and slurry	USPAT	2003/05/03 21:23
-	541	((((gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))) and (dielectric or interdielectric)) and (planariz$3 with ((dry adj etching) or CMP))) and (conductive with ((doped adj polysilicon) or titanium or (titanium adj nitride) or tungsten))) not (((((gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))) and (dielectric or interdielectric)) and (planariz$3 with ((dry adj etching) or CMP))) and (conductive with ((doped adj polysilicon) or titanium or (titanium adj nitride) or tungsten))) and slurry)	USPAT	2003/05/03 21:46
-	21	(self adj (aligned or aligning or aligns) adj (contact or contacts)) and ((stopping adj layer) with (nitride or (silicon adj nitride)))	USPAT	2003/05/03 21:48
-	1665	self adj (aligned or aligning or aligns) adj (contact or contacts)	USPAT	2003/05/03 21:54